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# 60 V, 310 mA N-channel Trench MOSFET Rev. 02 — 29 July 2010

**Product data sheet** 

#### **Product profile** 1.

#### **1.1 General description**

N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT323 (SC-70) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 1.2 Features and benefits

- AEC-Q101 qualified
- Logic-level compatible

#### 1.3 Applications

- High-speed line driver
- Low-side loadswitch

- Trench MOSFET technology
- Very fast switching
- Relay driver
- Switching circuits

#### 1.4 Quick reference data

#### Table 1. **Quick reference data**

Parameter	Conditions		Min	Тур	Max	Unit
drain-source voltage	T <sub>amb</sub> = 25 °C		-	-	60	V
gate-source voltage			-20	-	20	V
drain current	$V_{GS}$ = 10 V; $T_{amb}$ = 25 °C	<u>[1]</u>	-	-	310	mA
racteristics						
drain-source on-state resistance	$ \begin{array}{l} V_{GS} = 10 \text{ V; } I_D = 500 \text{ mA;} \\ T_j = 25 \ ^\circ\text{C}\text{; } t_p \leq 300  \mu\text{s}\text{; } \text{pulsed;} \\ \delta \leq 0.01 \end{array} $		-	1	1.6	Ω
	drain-source voltage gate-source voltage drain current racteristics drain-source on-state	$\begin{array}{c} \mbox{drain-source} \\ \mbox{voltage} \\ \mbox{gate-source} \\ \mbox{voltage} \\ \mbox{drain current} \\ \mbox{drain current} \\ \mbox{V}_{GS} = 10 \ \mbox{V}; \ \mbox{T}_{amb} = 25 \ \ \mbox{°C} \\ \mbox{racteristics} \\ \mbox{drain-source} \\ \mbox{on-state} \\ \mbox{V}_{GS} = 10 \ \ \mbox{V}; \ \mbox{I}_{D} = 500 \ \ \mbox{mA}; \\ \mbox{T}_{j} = 25 \ \ \ \mbox{°C}; \ \ \mbox{t}_{p} \leq 300 \ \ \mbox{µs}; \ \ \mbox{pulsed}; \end{array}$	$\begin{tabular}{ c c c c } \hline drain-source & voltage & & & & & & & & & & & & & & & & & & &$	$\begin{array}{c} \mbox{drain-source} \\ \mbox{voltage} \\ \mbox{gate-source} \\ \mbox{voltage} \\ \mbox{drain current} \\ \mbox{drain current} \\ \mbox{V}_{GS} = 10 \ \mbox{V}; \ \mbox{T}_{amb} = 25 \ \ \mbox{°C} \\ \mbox{fill} \\ \mbox{-20} \\ $	$\begin{array}{c} \text{drain-source} \\ \text{voltage} \\ \text{gate-source} \\ \text{voltage} \end{array} \xrightarrow{T_{amb} = 25 \ ^{\circ}\text{C}} & - & - \\ \hline -20 & -20 & -20 & - \\ \hline -20 & -$	$\begin{array}{c} \text{drain-source} \\ \text{voltage} \\ \text{gate-source} \\ \text{voltage} \\ \end{array}  \begin{array}{c} T_{amb} = 25 \ ^{\circ}\text{C} \\ \begin{array}{c} - & - \\ & 60 \\ \end{array} \\ \begin{array}{c} -20 \\ -20 \\ -20 \\ \end{array} \\ \begin{array}{c} -20 \\ 20 \\ \end{array} \\ \end{array} \\ \begin{array}{c} -20 \\ \end{array} \\ \begin{array}{c} -20 \\ 20 \\ \end{array} \\ \end{array} \\ \begin{array}{c} -20 \\ \end{array} \\ \begin{array}{c} -20 \\ 20 \\ \end{array} \\ \end{array} \\ \begin{array}{c} -20 \\ \end{array} \\ \end{array} \\ \end{array} \\ \begin{array}{c} -20 \\ \end{array} \\ \end{array} \\ \end{array} \\ \begin{array}{c} -20 \\ \end{array} \\ \end{array} \\ \end{array} \\ \end{array} \\ \end{array} \\ \end{array} \\ \begin{array}{c} -20 \\ \end{array} \\ \begin{array}{c} -20 \\ \end{array} \\ $

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



#### 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		-
2	S	source		
3	D	drain	1 ⊟ 2 SOT323 (SC-70)	G F S

#### 3. Ordering information

Table 3. Orderin	ng information		
Type number	Package		
	Name	Description	Version
2N7002PW	SC-70	plastic surface-mounted package; 3 leads	SOT323

#### 4. Marking

Table 4.   Marking codes	
Type number	Marking code <sup>[1]</sup>
2N7002PW	X8%

[1] % = -: made in Hong Kong; % = p: made in Hong Kong; % = t: made in Malaysia; % = W: made in China

#### 5. Limiting values

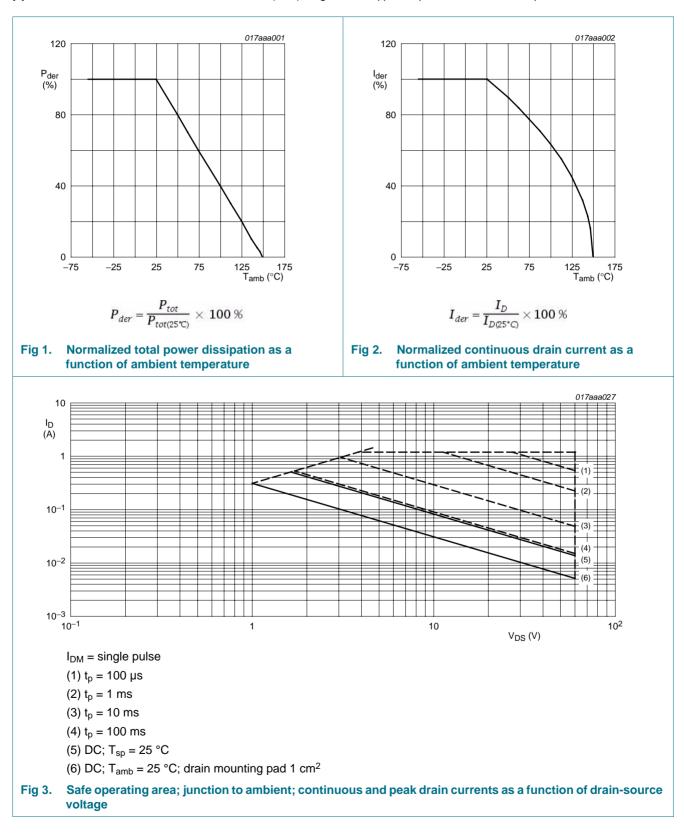
#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>amb</sub> = 25 °C		-	60	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	$V_{GS}$ = 10 V; $T_{amb}$ = 25 °C	<u>[1]</u>	-	310	mA
		$V_{GS}$ = 10 V; $T_{amb}$ = 100 °C	<u>[1]</u>	-	240	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	1.2	А
P <sub>tot</sub> to	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	260	mW
			[1]	-	310	mW
		T <sub>sp</sub> = 25 °C		-	830	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drai	in diode					
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	310	mA

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

2N7002PW



[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

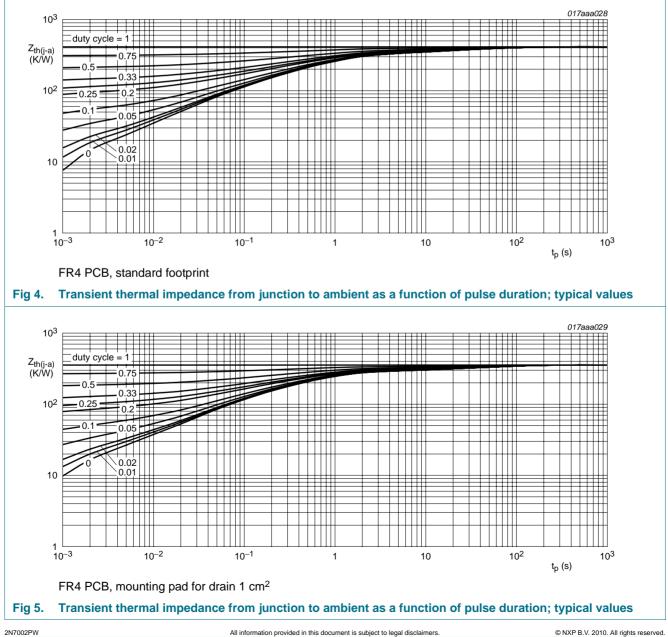
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#### Thermal characteristics 6.

Table 6.	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1]	-	415	480	K/W
	from junction to ambient		[2]	-	350	400	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	150	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

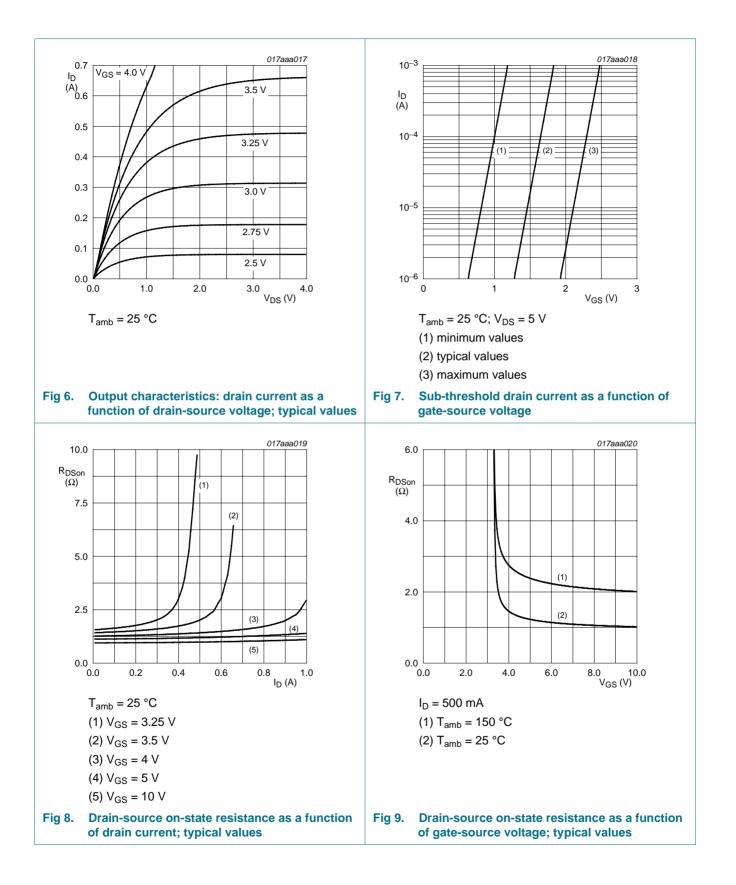
Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>. [2]



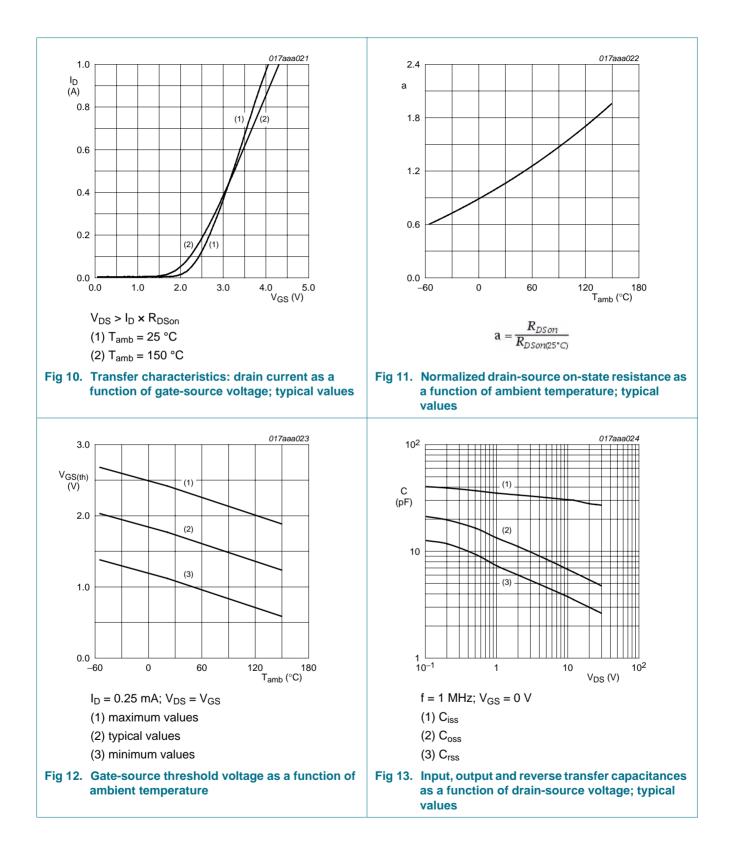
## 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = 10 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	60	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	1.1	1.75	2.4	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μA
		$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	10	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
		$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	100	nA
R <sub>DSon</sub> drain-source on-state resistance		$V_{GS} = 5 \text{ V}; I_D = 50 \text{ mA}; \text{ pulsed}; t_p \le 300  \mu\text{s}; \delta \le 0.01 ; T_j = 25 ^{\circ}\text{C}$	-	1.3	2	Ω
	$V_{GS}$ = 10 V; I <sub>D</sub> = 500 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.01 ; T <sub>j</sub> = 25 °C	-	1	1.6	Ω	
g <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 200 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.01 ; T <sub>j</sub> = 25 °C	-	400	-	mS
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D$ = 300 mA; $V_{DS}$ = 30 V; $V_{GS}$ = 4.5 V;	-	0.6	0.8	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.2	-	nC
$Q_{GD}$	gate-drain charge		-	0.2	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 V; V_{DS} = 10 V; f = 1 MHz;$	-	30	50	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	7	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	4	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 50 \text{ V}; \text{ R}_{L} = 250 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	3	6	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	4	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	10	20	ns
t <sub>f</sub>	fall time		-	5	-	ns
Source-d	rain diode					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 115 mA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	0.47	0.75	1.1	V

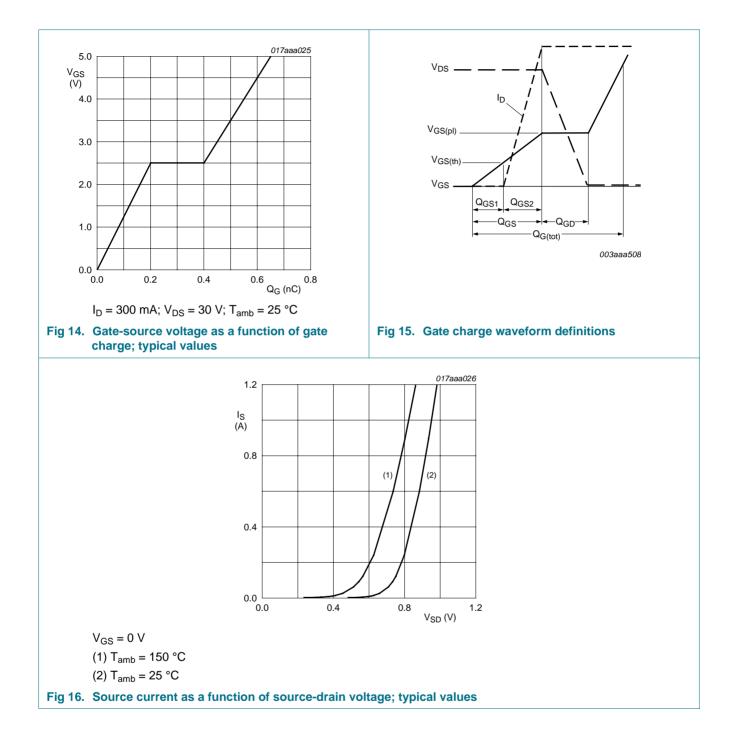
#### 60 V, 310 mA N-channel Trench MOSFET



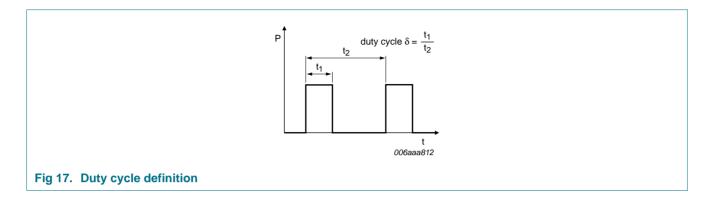
#### 60 V, 310 mA N-channel Trench MOSFET



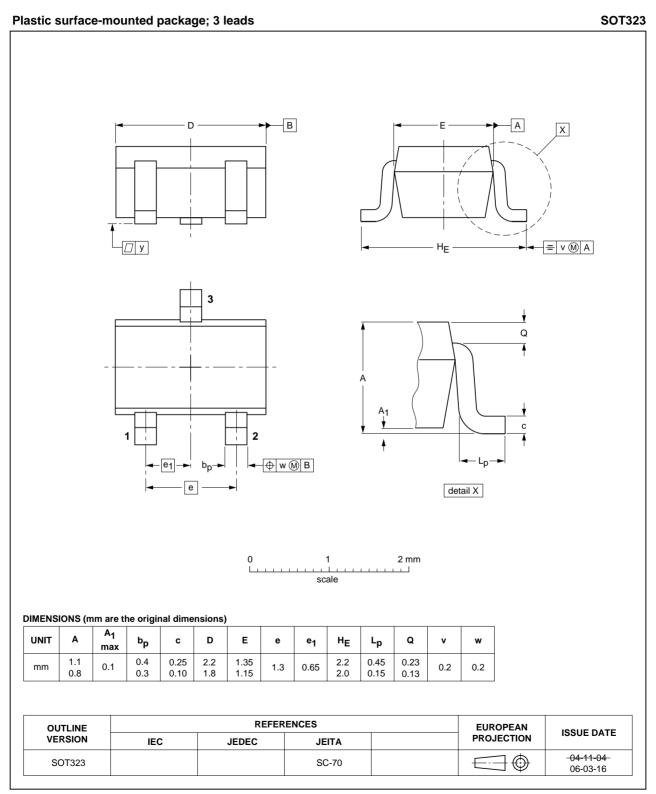
60 V, 310 mA N-channel Trench MOSFET



## 8. Test information



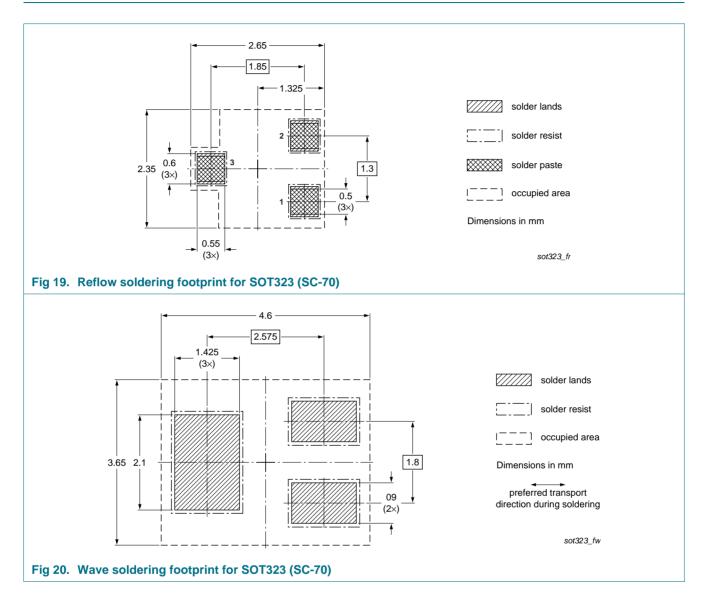
#### 9. Package outline



#### Fig 18. Package outline SOT323 (SC-70)

60 V, 310 mA N-channel Trench MOSFET

### **10. Soldering**



## **11. Revision history**

Table 8. Rev	ision history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
2N7002PW v.2	20100729	Product data sheet	-	2N7002PW_1
Modifications:	<ul> <li>Correction of the</li> </ul>	nermal values.		
	<ul> <li>Correction of value</li> </ul>	arious characteristics value	s including related gra	phs.
2N7002PW_1	20100422	Product data sheet	-	-

### **12. Legal information**

#### 12.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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